

09/747,848

Response to Office Action mailed January 16, 2002

11. (Amended) An ESD protection structure for use with RF frequency integrated circuits comprising:

- Q2
- a P- epitaxial silicon semiconductor substrate;
 - an N- well region disposed in the semiconductor substrate;
 - a P+ first region disposed in the N- well region on the P- epitaxial silicon semiconductor substrate; B
 - an N+ second region disposed in and on the P- epitaxial silicon semiconductor substrate and spaced apart from the P+ first region and the N- well; and
 - an electrical isolation region disposed in the P- epitaxial silicon semiconductor substrate between the P+ first region and the N+ second region.

Please add the following new claims:

- sub B2 >
- 12. An ESD protection structure formed in a semiconductor material of a first conductivity type, the structure comprising:
- a well region of a second conductivity type formed in the semiconductor material;
 - a first region of the first conductivity type formed in the well region;
 - a second region of the second conductivity type formed in the semiconductor material and spaced apart from the first region and the well; and
 - an electrical isolation region formed in the semiconductor substrate between the first region and the second region.
- A3

13. The structure of claim 12 wherein the substrate has a dopant concentration, and the first region has a dopant concentration greater than the dopant concentration of the substrate. C

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93 14. The structure of claim 13 wherein the well region has a dopant concentration,
and the second region has a dopant concentration greater than the dopant concentration of the
well region.-- c
